

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4	"254858".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 12:23
S2	0	2002-254858.pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 11:23
S3	10415	substrat\$3 with through\$3 with hol\$3 with electro\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 13:40
S4	1	S3 with DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 12:28
S5	3015	S3 with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:20
S6	25	S5 with Ion with Etching	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 14:05
S7	5164	substrat\$3 with through\$3 adj hol\$3 with electro\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 12:31
S8	1129	S7 with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 13:39
S12	300673	"257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 13:35
S14	2177	257/774.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:26

S15	41	S8 and S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 13:36
S17	4455	(substrat\$3 with through\$3 with hol\$3 with electro\$3).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 13:40
S20	1417	S14 and (insulating adj\$4 layer).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 14:02
S25	1	(interposer with stack\$3 adj devic\$4).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 14:52
S26	32	(small adj hole with semiconductor adj substrate).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 14:57
S27	1327	(electron with semiconductor adj substrate).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:12
S29	18381	S3 ans S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 14:58
S30	15	S3 and S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 14:59
S31	413	interposer with hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:50
S32	648	(stack\$3 with devic\$3 with substrate with electro\$3).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:07

S33	52	S32 with hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 11:33
S34	1	S32 with dielectric with lin\$3 with hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:10
S35	148	S32 with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:10
S36	411	S32 with wir\$3 sructur\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:11
S37	6	S36 with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:11
S38	0	S27 with singl\$3 adj layer with wir\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:13
S39	15362	Sekine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:14
S40	128	stack\$3 with devic\$3 with substrat\$2 adj5 hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:19
S41	18	S3 with semiconductor with penetrat\$4 adj5 hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 15:20
S42	1712	substrat\$3 with penetrat\$4 with substrat\$3 with hol\$3	USPAT	OR	OFF	2005/05/02 15:25
S43	380	S42 with semiconductor	USPAT	OR	OFF	2005/05/02 15:26
S44	58	S43 with silicon	USPAT	OR	OFF	2005/05/02 15:26

S45	1678276	sidewall with through adj\$2 hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:13
S46	1677558	sidewall with through adj\$1 hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:14
S47	5166	substrat\$3 with through\$3 adj hol\$3 with electro\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:14
S48	1130	S47 with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:14
S49	577122	S48 will S46	USPAT	OR	OFF	2005/05/03 09:15
S51	31	S46 with S48 with insulat\$4 adj layer	USPAT	OR	OFF	2005/05/03 09:19
S52	1166	insulat\$4 adj layer with through adj hole	USPAT	OR	OFF	2005/05/03 09:19
S53	293	S52 with substrate	USPAT	OR	OFF	2005/05/03 09:19
S54	14	S47 with sidewall\$2	USPAT	OR	OFF	2005/05/03 09:23
S55	49519	substrate with hol\$2	USPAT	OR	OFF	2005/05/03 09:24
S56	2186	257/774.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:24
S61	1497	S56	USPAT	OR	OFF	2005/05/03 09:25
S63	2186	257/774.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:27
S64	0	S63 with S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:27
S65	592	S63 and S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:27

S66	488	S65 and insulat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:28
S67	0	S65 and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:28
S68	1206	DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:28
S69	202	S68 and through adj hol\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:36
S70	190836	method with via	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:36
S71	7	S70 with DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:40
S72	125	S70 with backside	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:58
S73	11710	form\$3 with substrate with through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:59
S74	281	438/667.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:19
S76	167	National adj Semiconductor with via	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:24

S77	0	National adj Semiconductor with CS100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:20
S79	167	S76 with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:23
S80	12	S76 with device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:22
S83	20	S76 and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:28
S84	1	S83 and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:26
S85	20	S83 and via	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:26
S86	1	"1.0" adj line adj width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:27
S87	9982	level\$3 adj metal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:28
S88	873	S87 with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:29
S89	103	S88 with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 11:31

S90	37	S89 with interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:24
S91	205834	Koji adj\$1 Sajui	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:24
S92	171	S91 with Miyamoto	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:27
S99	0	S92 and interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:29
S10 0	16	S92 and hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:32
S10 1	2	"6239495".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:32
S10 2	17	"6239495"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:41
S10 3	3206	257/758.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:43
S10 4	0	S103 with etch\$3 with hol\$3 with substrat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:42
S10 5	0	S103 with hol\$3 with substrat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:42

S10 6	0	S103 with hol\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:42
S10 7	1398	S103 and etch\$3 and hol\$3 and substrat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:43
S10 8	0	S103 with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:44
S10 9	2752	S103 and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:44
S11 0	1337	S109 and hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:45
S11 1	0	S108 and electro\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:45
S11 2	0	S108 and stack\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:45
S11 3	0	S108 and stack\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 12:45
S11 4	0	"667".ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:01
S11 5	0	"667"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:03



S11 6	0	"667"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:03
S11 7	281	438/667.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:24
S11 8	865	438/702.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:24
S11 9	0	216/119.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:25
S12 0	342	438/119.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:25
S12 1	284	438/216.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:25
S12 2	1596	427/96.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:25
S12 3	323	427/97.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:25
S12 4	444	427/98.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:38
S12 5	117	427/99.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:26

S12 6	81	S124 and through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:45
S12 7	0	(S124 and through adj hole).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:30
S12 8	0	S124 and interpos43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:39
S12 9	1	S125 and through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:40
S13 0	172	S123 and through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:40
S13 1	188	S122 and through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:41
S13 2	2	S121 and through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:41
S13 3	7	S131 and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:43
S13 4	6	S130 and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:43
S13 5	81	S126 and through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:45

S13 6	4	S126 and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:46
S13 7	1298	216/13.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:47
S13 8	514	216/17.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:46
S13 9	84	216/19.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:47
S14 0	2583	216/67.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:47
S14 1	6	S137 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:49
S14 2	9	S138 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:50
S14 3	1	S139 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:50
S14 4	11	S140 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:56
S14 5	2143	29/846.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:52

S14 6	663	29/847.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:52
S14 7	2405	29/832.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:52
S14 8	3739	438/694.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:53
S14 9	374	438/695.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:53
S15 0	460	438/696.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:53
S15 1	942	438/700.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:53
S15 2	865	438/702.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:53
S15 3	430	438/703.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:53
S15 4	611	438/719.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:53
S15 5	569	438/639.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:53

S15 6	200	438/642.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:54
S15 7	275	438/644.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:54
S15 8	782	438/652.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:54
S15 9	331	438/654.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:54
S16 0	281	438/667.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:54
S16 1	34	S145 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:19
S16 2	9	S146 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:09
S16 3	24	S147 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:01
S16 4	10	S148 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:04
S16 5	2	S149 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:05

S16 6	1	S150 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:05
S16 7	3	S151 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:06
S16 8	8	S152 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:08
S16 9	2	S153 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:10
S17 0	3	S154 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:12
S17 1	7	S155 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:13
S17 2	0	S156 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:57
S17 3	1	S157 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:15
S17 4	8	S158 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:15
S17 5	0	S159 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:57

S17 6	23	S160 and through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:16
S17 7	0	S155 and S156 and S157 and S158 and S159 and S159	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:12
S17 9	16637	bga	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:20
S18 0	3660	S179 and electrode\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:20
S18 1	852	S180 and through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:22
S18 2	3	S180 and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:21
S18 3	104	S181 and interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:28
S18 4	2856507	making adj hole adj\$4 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:28
S18 5	1338441	mak\$3 adj hole adj\$4 substrate with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:29
S18 6	430	S185 and S181	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:29

S18 7	62	S186 and interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:31
S18 8	909086	adhesive layer and interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:31
S18 9	907978	adhesive layer with interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:31
S19 0	45195	S189 and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:32
S19 1	1865	S190 and liner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:32
S19 2	602	S191 and hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:32
S19 3	258	S192 and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:32
S19 4	258	S193 and adhesi\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:34
S19 5	38	metal adj interconnect with through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:34
S19 6	904277	silicon adk substrate with through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:42



S19 7	99	silicon adj substrate with through adj hole with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 17:42
S19 8	79	interposer with silicon adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:05
S19 9	0	conductice with hole with silicon adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:06
S20 0	322	conductive with hole with silicon adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:06
S20 1	38	S200 with through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:09
S20 2	6	metal adj top adj layer with via	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:12
S20 3	7714	metal adj layer with via	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:16
S20 4	525	S203 with interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:14
S20 5	5	"6080660"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:16
S20 6	1570	S203 with hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:16

S20 7	82	S204 with hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:19
S20 8	2	dielectric with lined with hole with top with metal adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:22
S20 9	0	dielectric with lined with hole with top with metal adj pads	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:21
S21 0	0	hole with dielectric with lin\$3 with metal adj pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 18:23
S21 1	215	hole with metal adj pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 07:54
S21 2	1498	through adj hole with dielectric with layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 07:55
S21 3	320	S212 with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 07:56
S21 4	1	S213 with silicon adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 07:57
S21 5	8	silicon adj substrate with dielectric with layer with through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 07:59
S21 6	108	bga with silicon with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:04

S21 7	2	S216 with dielectric with layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:00
S21 8	4	S216 with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:06
S21 9	0	S216 with insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:04
S22 0	0	through adj hole with to with insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:06
S22 1	0	electrode with hole with to with insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:07
S22 2	32244	electrode with insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:07
S22 3	2	silicon adj substrate with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:08
S22 4	5	through with silicon adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:09
S22 5	452	interposer with silicon withsubstrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:11
S22 6	22	S225 with insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:31

S22 7	41	S225 with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:11
S22 8	1637710	etch adj\$2 silicon with stop adj\$4 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:38
S22 9	41	S227 with interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:35
S23 0	14035	S228 with through with hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:38
S23 1	7213	S228 with through adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 10:06
S23 2	2	"6864172"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 11:36
S23 4	64	Bosch with DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 11:33
S23 5	0	Bosch with (DRIE.ab.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 11:33
S23 6	0	"6864172.pn"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 11:36
S23 7	2	"6864172".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 11:36